

# Dual 2-to-4 Decoder/ Demultiplexer

## MC74VHCT139A

The MC74VHCT139A is an advanced high speed CMOS 2-to-4 decoder/demultiplexer fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL devices while maintaining CMOS low power dissipation.

When the device is enabled ( $\bar{E}$  = low), it can be used for gating or as a data input for demultiplexing operations. When the enable input is held high, all four outputs are fixed high, independent of other inputs.

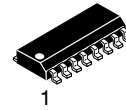
The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output.

The device output is compatible with TTL-type input thresholds and the output has a full 5.0 V CMOS level output swing. The input protection circuitry on this device allows overvoltage tolerance on the input, allowing the device to be used as a logic-level translator from 3.0 V CMOS logic to 5.0 V CMOS logic, or from 1.8 V CMOS logic to 3.0 V CMOS logic while operating at the high-voltage power supply.

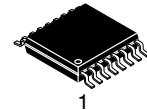
The MC74VHCT139A input structure provides protection when voltages up to 7.0 V are applied, regardless of the supply voltage. This allows the MC74VHCT139A to be used to interface 5.0 V circuits to 3.0 V circuits. The output structures also provide protection when  $V_{CC} = 0$  V. These input and output structures help prevent device destruction caused by supply voltage-input/output voltage mismatch, battery backup, hot insertion, etc.

### Features

- High Speed:  $t_{PD} = 5.0$  ns (Typ) at  $V_{CC} = 5.0$  V
- Low Power Dissipation:  $I_{CC} = 4$   $\mu$ A (Max) at  $T_A = 25^\circ$ C
- TTL-Compatible Inputs:  $V_{IL} = 0.8$  V;  $V_{IH} = 2.0$  V
- Power Down Protection Provided on Inputs and Outputs
- Balanced Propagation Delays
- Designed for 2.0 V to 5.5 V Operating Range
- Low Noise:  $V_{OLP} = 0.8$  V (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance:
  - Human Body Model > 2000 V;
  - Machine Model > 200 V
- Chip Complexity: 100 FETs or 25 Equivalent Gates
- These Devices are Pb-Free and are RoHS Compliant

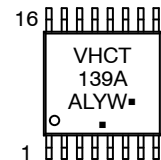
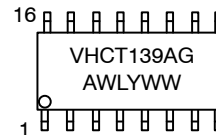


SOIC-16  
D SUFFIX  
CASE 751B



TSSOP-16  
DT SUFFIX  
CASE 948F

### MARKING DIAGRAM



A = Assembly Location  
 WL, L = Wafer Lot  
 Y = Year  
 WW, W = Work Week  
 G or  $\blacksquare$  = Pb-Free Package

(Note: Microdot may be in either location)

### FUNCTION TABLE

Inputs			Outputs			
$\bar{E}$	A1	A0	Y0	Y1	Y2	Y3
H	X	X	H	H	H	H
L	L	L	L	H	H	H
L	L	H	H	L	H	H
L	H	L	H	H	L	H
L	H	H	H	H	H	L

### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

# MC74VHCT139A

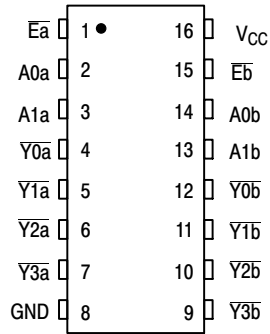


Figure 1. Pin Assignment

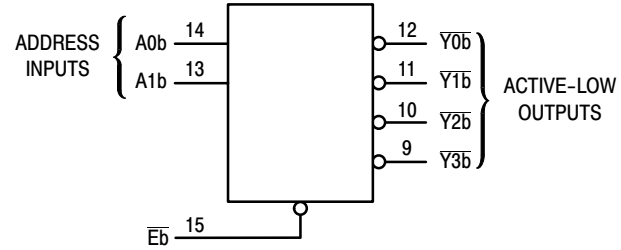
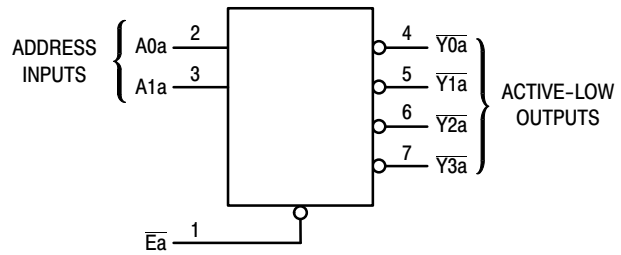


Figure 2. Logic Diagram

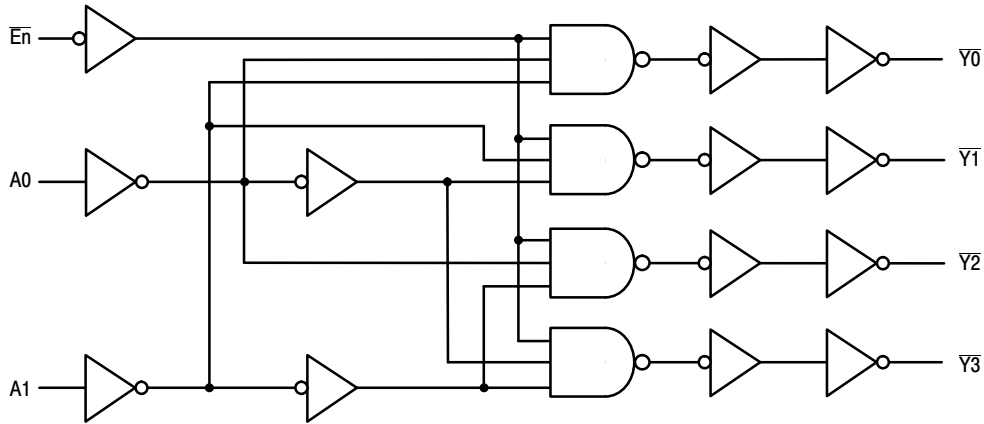


Figure 3. Expanded Logic Diagram  
(1/2 of Device)

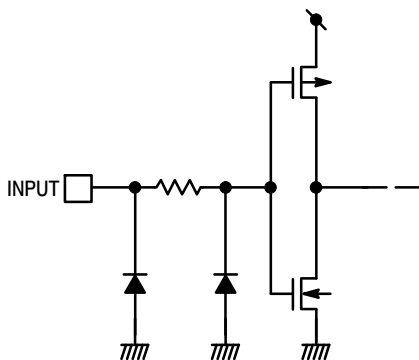


Figure 4. Input Equivalent Circuit

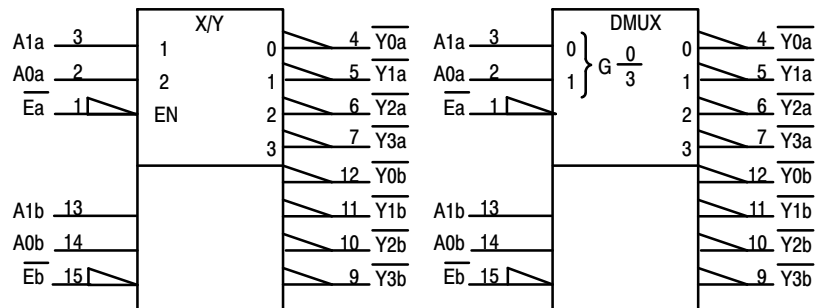


Figure 5. IEC Logic Diagram

# MC74VHCT139A

## MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
$V_{CC}$	Positive DC Supply Voltage	-0.5 to +7.0	V
$V_{IN}$	Digital Input Voltage	-0.5 to +7.0	V
$V_{OUT}$	DC Output Voltage Output in 3-State High or Low State	-0.5 to +7.0 -0.5 to $V_{CC} + 0.5$	V
$I_{IK}$	Input Diode Current	-20	mA
$I_{OK}$	Output Diode Current	$\pm 20$	mA
$I_{OUT}$	DC Output Current, per Pin	$\pm 25$	mA
$I_{CC}$	DC Supply Current, $V_{CC}$ and GND Pins	$\pm 75$	mA
$P_D$	Power Dissipation in Still Air SOIC TSSOP	200 180	mW
$T_{STG}$	Storage Temperature Range	-65 to +150	°C
$V_{ESD}$	ESD Withstand Voltage Human Body Model (Note 1) Machine Model (Note 2) Charged Device Model (Note 3)	>2000 >200 >2000	V
$I_{LATCHUP}$	Latchup Performance Above $V_{CC}$ and Below GND at 125°C (Note 4)	$\pm 300$	mA
$\theta_{JA}$	Thermal Resistance, Junction-to-Ambient SOIC TSSOP	143 164	°C/W

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Tested to EIA/JESD22-A114-A
2. Tested to EIA/JESD22-A115-A
3. Tested to JESD22-C101-A
4. Tested to EIA/JESD78

## RECOMMENDED OPERATING CONDITIONS

Symbol	Characteristics	Min	Max	Unit
$V_{CC}$	DC Supply Voltage	4.5	5.5	V
$V_{IN}$	DC Input Voltage	0	5.5	V
$V_{OUT}$	DC Output Voltage Output in 3-State High or Low State	0 0	5.5 $V_{CC}$	V
$T_A$	Operating Temperature Range, all Package Types	-55	125	°C
$t_r, t_f$	Input Rise or Fall Time $V_{CC} = 5.0 \text{ V} \pm 0.5 \text{ V}$	0	20	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

## DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

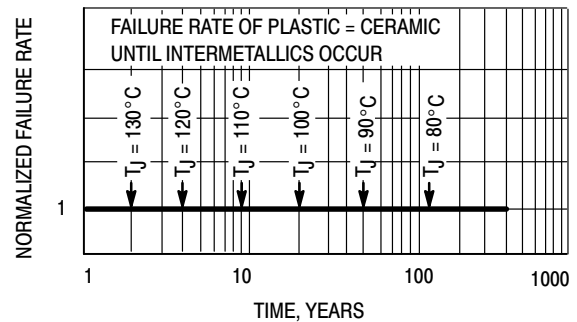


Figure 6. Failure Rate vs. Time Junction Temperature

# MC74VHCT139A

## DC CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Condition	V <sub>CC</sub> (V)	T <sub>A</sub> = 25°C			T <sub>A</sub> ≤ 85°C		T <sub>A</sub> = -55 to 125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
V <sub>IH</sub>	Minimum High-Level Input Voltage		4.5 to 5.5	2			2		2		V
V <sub>IL</sub>	Maximum Low-Level Input Voltage		4.5 to 5.5			0.8		0.8		0.8	V
V <sub>OH</sub>	Maximum High-Level Output Voltage	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub> I <sub>OH</sub> = -50 μA	4.5	4.4	4.5		4.4		4.4		V
		V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub> I <sub>OH</sub> = -8 mA	4.5	3.94			3.8		3.66		
V <sub>OL</sub>	Maximum Low-Level Output Voltage	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub> I <sub>OL</sub> = 50 μA	4.5		0	0.1		0.1		0.1	V
		V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub> I <sub>OL</sub> = 8 mA	4.5			0.36		0.44		0.52	
I <sub>IN</sub>	Input Leakage Current	V <sub>IN</sub> = 5.5 V or GND	0 to 5.5			±0.1		±1.0		±1.0	μA
I <sub>CC</sub>	Maximum Quiescent Supply Current	V <sub>IN</sub> = V <sub>CC</sub> or GND	5.5			4.0		40.0		40.0	μA
I <sub>CCT</sub>	Additional Quiescent Supply Current (per Pin)	Any one input: V <sub>IN</sub> = 3.4 V All other inputs: V <sub>IN</sub> = V <sub>CC</sub> or GND	5.5			1.35		1.5		1.5	μA
I <sub>OPD</sub>	Output Leakage Current	V <sub>OUT</sub> = 5.5 V	0			0.5		5		5	μA

## AC ELECTRICAL CHARACTERISTICS (Input t<sub>r</sub> = t<sub>f</sub> = 3.0ns)

Symbol	Parameter	Test Conditions	T <sub>A</sub> = 25°C			T <sub>A</sub> ≤ 85°C		T <sub>A</sub> = -55 to 125°C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, A to Y	V <sub>CC</sub> = 3.3 ± 0.3 V C <sub>L</sub> = 15 pF C <sub>L</sub> = 50 pF		7.2 9.7	11.0 14.5	1.0 1.0	13.0 16.5	1.0 1.0	13.0 16.5	ns
		V <sub>CC</sub> = 5.0 ± 0.5 V C <sub>L</sub> = 15 pF C <sub>L</sub> = 50 pF		5.0 6.5	7.2 9.2	1.0 1.0	8.5 10.5	1.0 1.0	8.5 10.5	
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, E to Y	V <sub>CC</sub> = 3.3 ± 0.3 V C <sub>L</sub> = 15 pF C <sub>L</sub> = 50 pF		6.4 8.9	9.2 12.7	1.0 1.0	11.0 14.5	1.0 1.0	11.0 14.5	ns
		V <sub>CC</sub> = 5.0 ± 0.5 V C <sub>L</sub> = 15 pF C <sub>L</sub> = 50 pF		4.4 5.9	6.3 8.3	1.0 1.0	7.5 9.5	1.0 1.0	7.5 9.5	
C <sub>IN</sub>	Maximum Input Capacitance			4	10		10		10	pF

C <sub>PD</sub>	Power Dissipation Capacitance (Note 5)	Typical @ 25°C, V <sub>CC</sub> = 5.0V	pF
		26	

5. C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I<sub>CC(OPR)</sub> = C<sub>PD</sub> • V<sub>CC</sub> • f<sub>in</sub> + I<sub>CC</sub>/2 (per decoder). C<sub>PD</sub> is used to determine the no-load dynamic power consumption; P<sub>D</sub> = C<sub>PD</sub> • V<sub>CC</sub><sup>2</sup> • f<sub>in</sub> + I<sub>CC</sub> • V<sub>CC</sub>.

# MC74VHCT139A

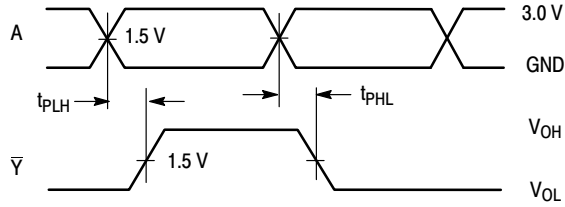


Figure 7. Switching Waveform

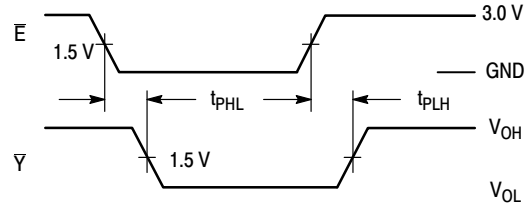
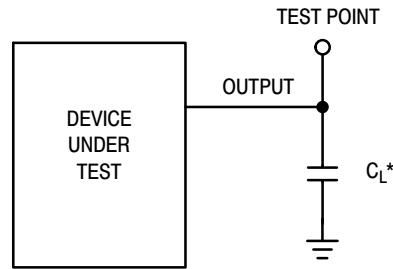


Figure 8. Switching Waveform



\*Includes all probe and jig capacitance

Figure 9. Test Circuit

## ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
MC74VHCT139ADG	SOIC-16 (Pb-Free)	48 Units / Rail
MC74VHCT139ADR2G	SOIC-16 (Pb-Free)	2500 Tape & Reel
MC74VHCT139ADTG	TSSOP-16 (Pb-Free)	96 Units / Rail
MC74VHCT139ADTRG	TSSOP-16 (Pb-Free)	2500 Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).


**SOIC-16 9.90x3.90x1.37 1.27P**  
**CASE 751B**  
**ISSUE M**

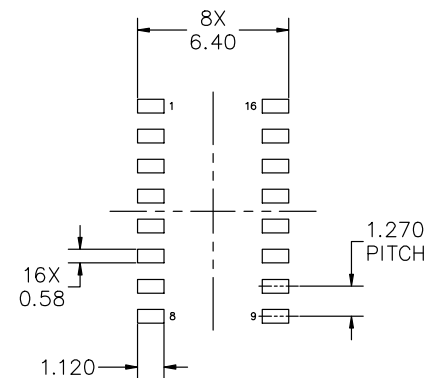
DATE 18 OCT 2024

## NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. DIMENSION IN MILLIMETERS. ANGLE IN DEGREES.
3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15mm PER SIDE.
5. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127mm TOTAL IN EXCESS OF THE b DIMENSION AT MAXIMUM MATERIAL CONDITION.



MILLIMETERS			
DIM	MIN	NOM	MAX
A	1.35	1.55	1.75
A1	0.10	0.18	0.25
A2	1.25	1.37	1.50
b	0.35	0.42	0.49
c	0.19	0.22	0.25
D	9.90 BSC		
E	6.00 BSC		
E1	3.90 BSC		
e	1.27 BSC		
h	0.25	---	0.50
L	0.40	0.83	1.25
L1	1.05 REF		
θ	0°	---	7°
TOLERANCE OF FORM AND POSITION			
aaa	0.10		
bbb	0.20		
ccc	0.10		
ddd	0.25		
eee	0.10		



\*FOR ADDITIONAL INFORMATION ON OUR  
PB-FREE STRATEGY AND SOLDERING DETAILS,  
PLEASE DOWNLOAD THE onsemi SOLDERING  
AND MOUNTING TECHNIQUES REFERENCE  
MANUAL, SOLDERM/D

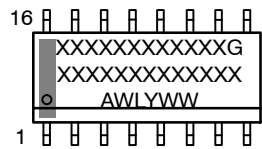
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SOIC-16 9.90x3.90x1.37 1.27P  
CASE 751B  
ISSUE M

DATE 18 OCT 2024

GENERIC  
MARKING DIAGRAM\*



XXXXX = Specific Device Code  
A = Assembly Location  
WL = Wafer Lot  
Y = Year  
WW = Work Week  
G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1: PIN 1. COLLECTOR 2. BASE 3. EMITTER 4. NO CONNECTION 5. EMITTER 6. BASE 7. COLLECTOR 8. COLLECTOR 9. BASE 10. EMITTER 11. NO CONNECTION 12. EMITTER 13. BASE 14. COLLECTOR 15. EMITTER 16. COLLECTOR	STYLE 2: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION 4. CATHODE 5. CATHODE 6. NO CONNECTION 7. ANODE 8. CATHODE 9. CATHODE 10. ANODE 11. NO CONNECTION 12. CATHODE 13. CATHODE 14. NO CONNECTION 15. ANODE 16. CATHODE	STYLE 3: PIN 1. COLLECTOR, DYE #1 2. BASE, #1 3. EMITTER, #1 4. COLLECTOR, #1 5. COLLECTOR, #2 6. BASE, #2 7. EMITTER, #2 8. COLLECTOR, #2 9. COLLECTOR, #3 10. BASE, #3 11. EMITTER, #3 12. COLLECTOR, #3 13. COLLECTOR, #4 14. BASE, #4 15. EMITTER, #4 16. COLLECTOR, #4	STYLE 4: PIN 1. COLLECTOR, DYE #1 2. COLLECTOR, #1 3. COLLECTOR, #2 4. COLLECTOR, #2 5. COLLECTOR, #3 6. COLLECTOR, #3 7. COLLECTOR, #4 8. COLLECTOR, #4 9. BASE, #4 10. EMITTER, #4 11. BASE, #3 12. EMITTER, #3 13. BASE, #2 14. EMITTER, #2 15. BASE, #1 16. EMITTER, #1
STYLE 5: PIN 1. DRAIN, DYE #1 2. DRAIN, #1 3. DRAIN, #2 4. DRAIN, #2 5. DRAIN, #3 6. DRAIN, #3 7. DRAIN, #4 8. DRAIN, #4 9. GATE, #4 10. SOURCE, #4 11. GATE, #3 12. SOURCE, #3 13. GATE, #2 14. SOURCE, #2 15. GATE, #1 16. SOURCE, #1	STYLE 6: PIN 1. CATHODE 2. CATHODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE 7. CATHODE 8. CATHODE 9. ANODE 10. ANODE 11. ANODE 12. ANODE 13. ANODE 14. ANODE 15. ANODE 16. ANODE	STYLE 7: PIN 1. SOURCE N-CH 2. COMMON DRAIN (OUTPUT) 3. COMMON DRAIN (OUTPUT) 4. GATE P-CH 5. COMMON DRAIN (OUTPUT) 6. COMMON DRAIN (OUTPUT) 7. COMMON DRAIN (OUTPUT) 8. SOURCE P-CH 9. SOURCE P-CH 10. COMMON DRAIN (OUTPUT) 11. COMMON DRAIN (OUTPUT) 12. COMMON DRAIN (OUTPUT) 13. GATE N-CH 14. COMMON DRAIN (OUTPUT) 15. COMMON DRAIN (OUTPUT) 16. SOURCE N-CH	

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**TSSOP-16 WB**  
**CASE 948F**  
**ISSUE B**

DATE 19 OCT 2006

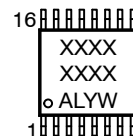

**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	---	1.20	---	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.18	0.28	0.007	0.011
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

**RECOMMENDED  
SOLDERING FOOTPRINT\***


\*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

**GENERIC  
MARKING DIAGRAM\***


XXXX = Specific Device Code  
A = Assembly Location  
L = Wafer Lot  
Y = Year  
W = Work Week  
G or ■ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

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